

WHAT IS CLAIMED IS:

1. A stacked type semiconductor device comprising  
a predetermined semiconductor integrated circuit chip  
and at least one semiconductor integrated circuit chip  
5 which are stacked,

said at least one semiconductor integrated circuit  
chip including a group of circuit blocks, and

10 the predetermined semiconductor integrated circuit  
chip comprising a storage section configured to store  
defect information indicative of a defective circuit  
block if the group includes the defective circuit block  
and a replacement circuit section configured to replace  
the defective circuit block.

15 2. The stacked type semiconductor device  
according to claim 1, wherein the circuit blocks  
included in the group are logic circuit blocks.

20 3. The stacked type semiconductor device  
according to claim 2, wherein the replacement circuit  
section has a circuit equivalent to the defective  
circuit block.

25 4. The stacked type semiconductor device  
according to claim 3, wherein the circuit equivalent to  
the defective circuit block is produced after the  
predetermined semiconductor integrated circuit chip and  
said at least one semiconductor integrated circuit chip  
have been stacked.

5. The stacked type semiconductor device

according to claim 2, wherein the replacement circuit section has a configuration capable of producing a circuit equivalent to each of the circuit blocks included in the group.

5       6. The stacked type semiconductor device according to claim 1, wherein the circuit blocks included in the group are memory circuit blocks.

10      7. The stacked type semiconductor device according to claim 6, wherein each of the circuit blocks included in the group has an equivalent circuit.

8. The stacked type semiconductor device according to claim 7, wherein the replacement circuit section has a circuit equivalent to each of the circuit blocks included in the group.

15      9. The stacked type semiconductor device according to claim 6, wherein the predetermined semiconductor integrated circuit chip further comprises a selecting section configured to select the replacement circuit section by receiving access information used to access the defective circuit block.

20      10. The stacked type semiconductor device according to claim 9, wherein the selecting section selects the replacement circuit section in accordance with higher bit of an address signal for said at least one semiconductor integrated circuit chip and the defect information stored in the storage section.

25      11. The stacked type semiconductor device

according to claim 10, wherein lower bits of the address signal are used to select a memory cell in the memory circuit block.

12. The stacked type semiconductor device  
5 according to claim 11, wherein the lower bits of the address signal are inputted to the replacement circuit section of the predetermined semiconductor integrated circuit chip.

13. The stacked type semiconductor device  
10 according to claim 1, wherein said least one semiconductor integrated circuit chip includes an input and output control section configured to control an input and output relationship between the circuit blocks included in the group and the replacement circuit section by receiving the defect information.  
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14. The stacked type semiconductor device  
according to claim 1, wherein said at least one semiconductor integrated circuit chip includes a selecting section configured to select the replacement circuit section by receiving the defect information.  
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15. The stacked type semiconductor device  
according to claim 1, wherein the storage section stores the defect information after the predetermined semiconductor integrated circuit chip and said at least one semiconductor integrated circuit chip have been stacked.  
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16. The stacked type semiconductor device  
according to claim 1, wherein the storage section  
stores information indicating that the group does not  
include any defective circuit blocks if the group does  
5 not include any defective circuit blocks.

17. The stacked type semiconductor device  
according to claim 1, wherein the storage section  
includes a fuse portion arranged at a predetermined  
position which can be externally irradiated with  
10 an energy beam.

18. The stacked type semiconductor device  
according to claim 17, wherein the predetermined  
position is within an area in which the predetermined  
semiconductor integrated circuit chip does not overlap  
15 said at least one semiconductor integrated circuit  
chip.

19. The stacked type semiconductor device  
according to claim 1, wherein said at least one  
semiconductor integrated circuit chip includes at least  
20 two semiconductor integrated circuit chips.

20. The stacked type semiconductor device  
according to claim 19, wherein each of said at least  
two semiconductor integrated circuit chips is capable  
of using the replacement circuit section.